

Name: Ahmad Saraei

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## Education

### BSc.

University: Semnan University

Major: Solid State Physics

### Msc.

University: Materials and Energy Research Center

Major: Thin film Physics

Thesis: Design and Implementation of Method Based on Electrical Measurements for Estimation of Concentration Profile of Diffused Phosphorus in Silicon.

Supervisors: Dr. Mohamad Javad Eshraghi and Dr. Fariba Tajabadi

### PhD

University: Sharif University of Technology

Major: Nanotechnology

### Research Experience:

Solar Cells

Anodizing

Thin Films Fabrication

Resistive Switching

Electrochemical Characterization



**Honors & Awards:**

Ranked 4<sup>th</sup> in national university entrance exam for PhD degree in (Nanophysics) in year 2020

**Publications:**

- 1) Saraei, A., Eshraghi, M. J., Tajabadi, F., & Massoudi, A. (2018). ECV Doping Profile Measurements in Silicon Using Conventional Potentiostat. *Journal of Electronic Materials*, 47(12), 7309-7315.
- 2) Saraei, A., Eshraghi, M. J., Tajabadi, F., & Massoudi, A. (2017). Implementation of EIS for dopant profile analysis in n-type silicon. *Advanced Ceramics Progress*, 3(1), 16-20.
- 3) Saraei, A., Eshraghi, M., & Massoudi, A. (2016). Investigation of resistive switching in anodized titanium dioxide thin films. *Advanced Ceramics Progress*, 2(3), 34-37.
- 4) Saraei, A., Eshraghi, M. J., Tajabadi, F., & Massoudi, A., Implementing Potentiostat for Electrochemical Capacitance Voltage Dopant Profiling. 12<sup>th</sup> Annual Electrochemistry Seminar of Iran, 16 & 17 November 2016, Tarbiat Modares University.

**Patent:**

- 1) Saraei, A., Eshraghi, M. J., Device and Algorithm for Measuring Doping Concentration Profile in Semiconductors, Patent Number in Iran 93707.